High Current Transistors NPN Silicon

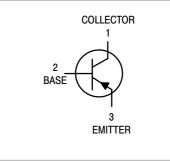
Features

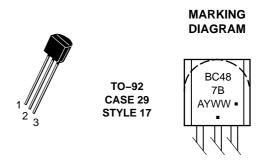
• Pb–Free Packages are Available*

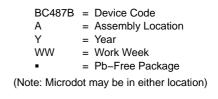


ON Semiconductor®

http://onsemi.com







ORDERING INFORMATION

Device	Package	Shipping [†]
BC487	TO-92	5000 Units / Box
BC487G	TO–92 (Pb–Free)	5000 Units / Box
BC487B	TO-92	5000 Units / Box
BC487BG	TO–92 (Pb–Free)	5000 Units / Box
BC487BRL1	TO-92	2000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS

MAXIMUM RATINGS					
Rating	Symbol	Value	Unit		
Collector – Emitter Voltage	V _{CEO}	60	Vdc		
Collector – Base Voltage	V _{CBO}	60	Vdc		
Emitter – Base Voltage	V _{EBO}	5.0	Vdc		
Collector Current – Continuous	Ι _C	0.5	Adc		
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	P _D	625 5.0	mW mW/°C		
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C		

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

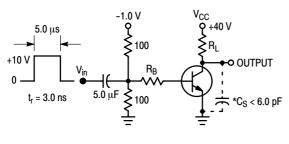
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	200	°C/W
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	83.3	°C/W

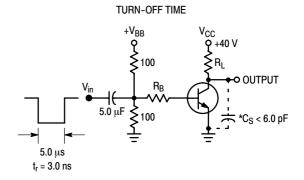
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = 10 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	60	-	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	V _{(BR)CBO}	60	-	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 40 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	_	100	nAdc
ON CHARACTERISTICS*					
$\label{eq:loss} \begin{array}{l} \text{DC Current Gain} \\ (I_C = 10 \text{ mAdc}, \text{ V}_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 100 \text{ mAdc}, \text{ V}_{CE} = 2.0 \text{ Vdc}) \\ & \text{BC487B} \\ (I_C = 1.0 \text{ Adc}, \text{ V}_{CE} = 5.0 \text{ Vdc})^* \end{array}$	h _{FE}	40 60 160 15	- - 260 -	- 400 400 -	_
Collector – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$)	V _{CE(sat)}		0.2 0.3	0.5 -	Vdc
Base – Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$) ⁽¹⁾	V _{BE(sat)}		0.85 0.9	1.2 -	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product (I _C = 50 mAdc, V_{CE} = 2.0 Vdc, f = 100 MHz)	f _T	-	200	-	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{ob}	-	7.0	-	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C _{ib}	-	50	-	pF

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.







*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

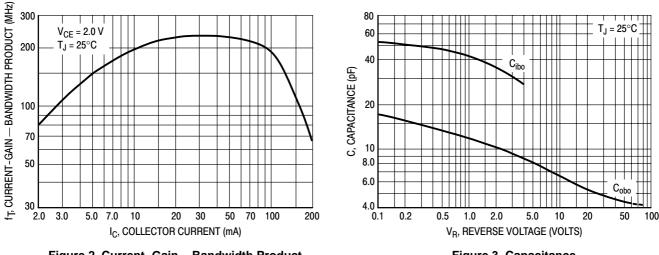
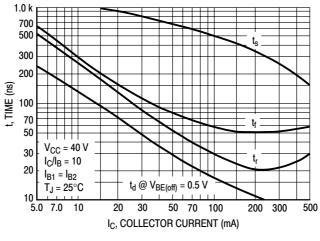
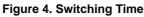




Figure 3. Capacitance





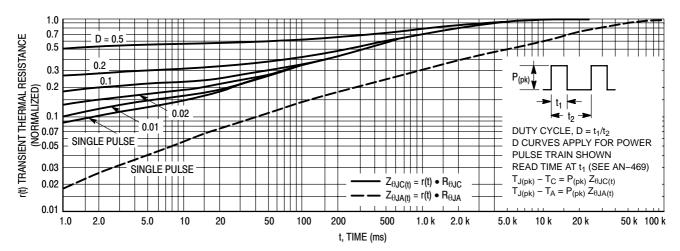


Figure 5. Thermal Response

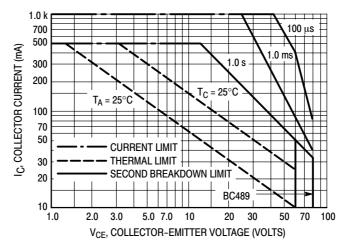
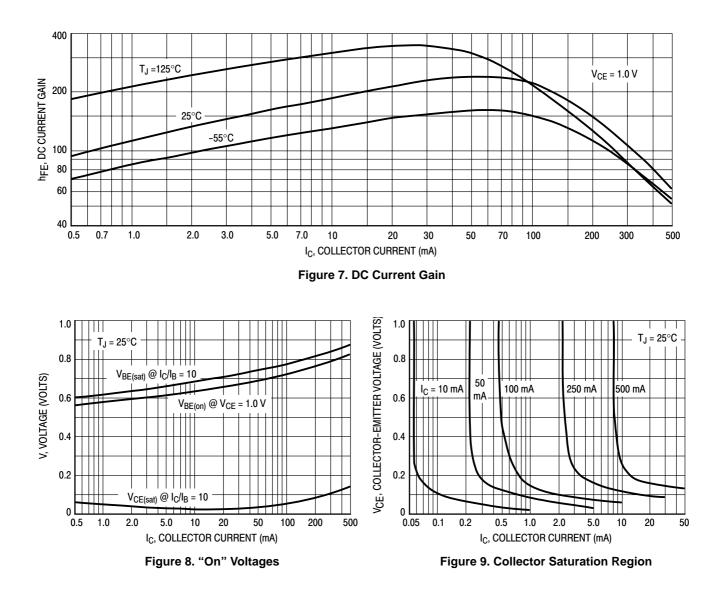
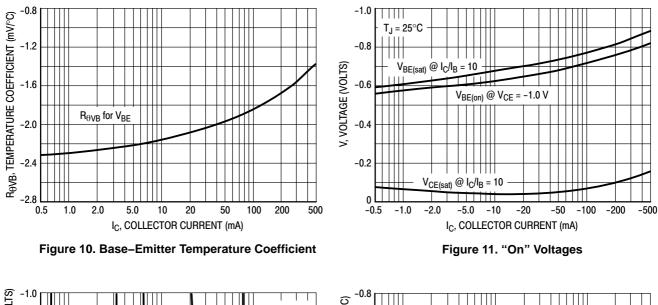


Figure 6. Active Region – Safe Operating Area





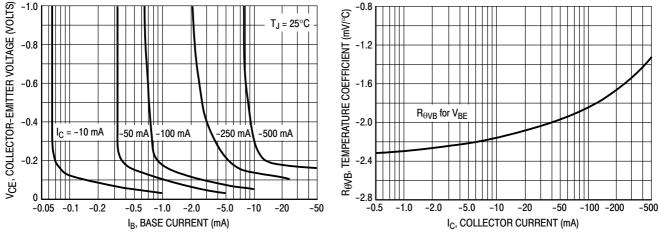
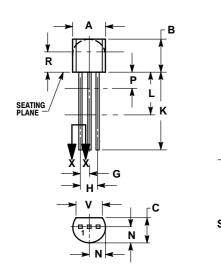


Figure 12. Collector Saturation Region

Figure 13. Base–Emitter Temperature Coefficient

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 17:

PIN 1. COLLECTOR 2. BASE 3. EMITTER

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